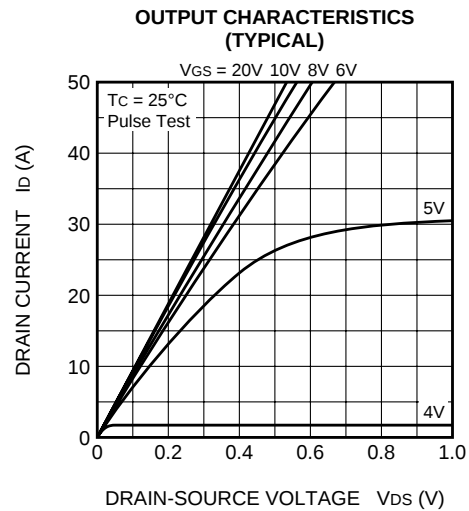
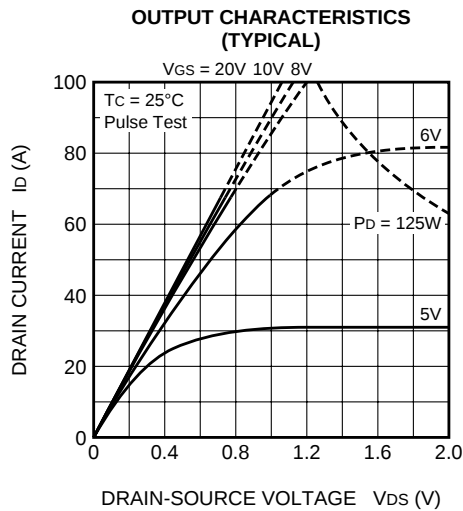
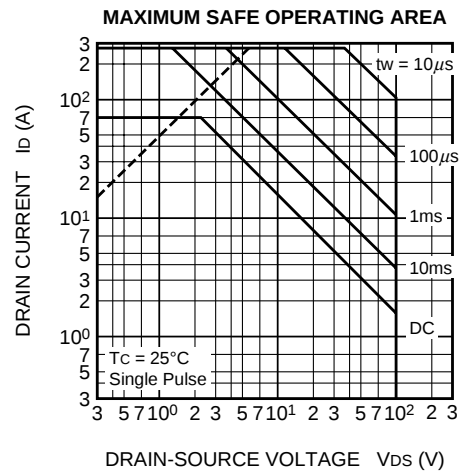
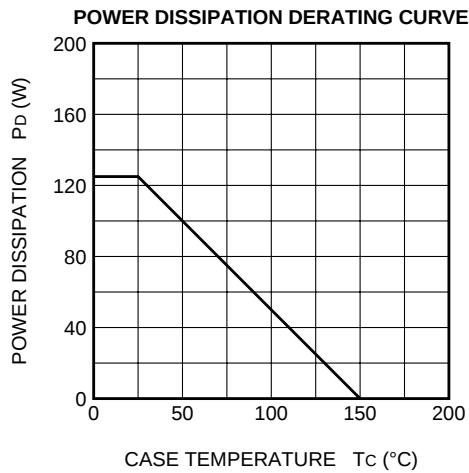
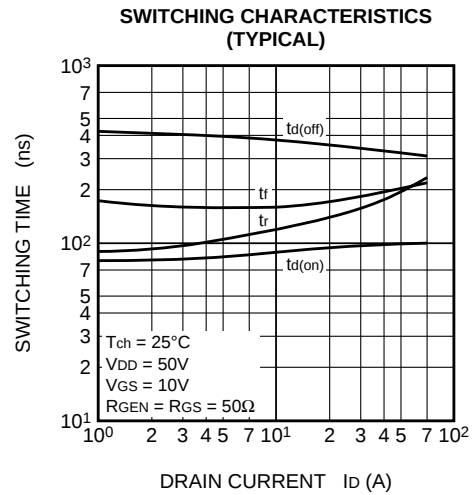
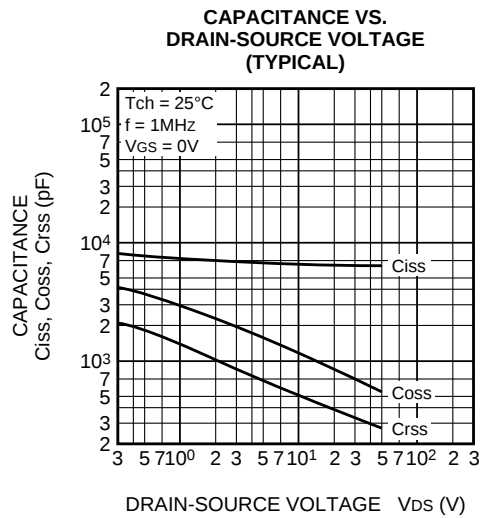
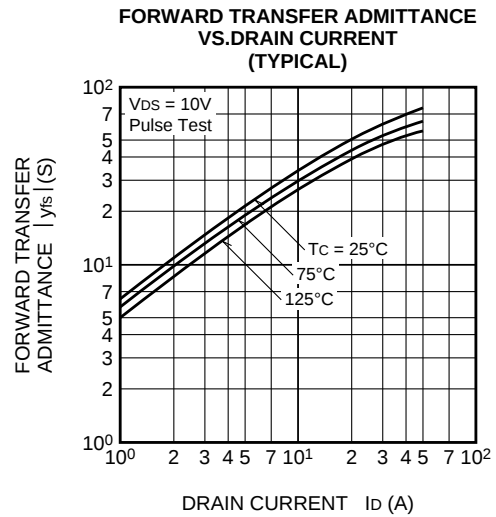
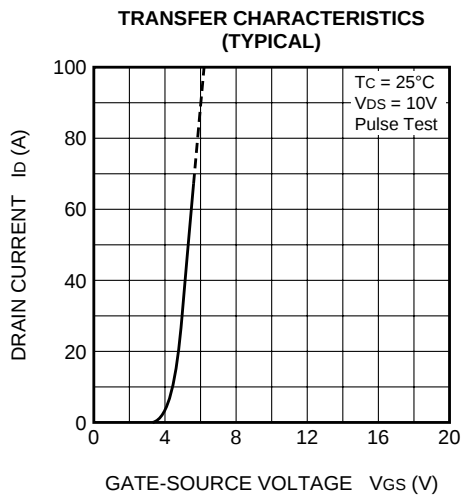
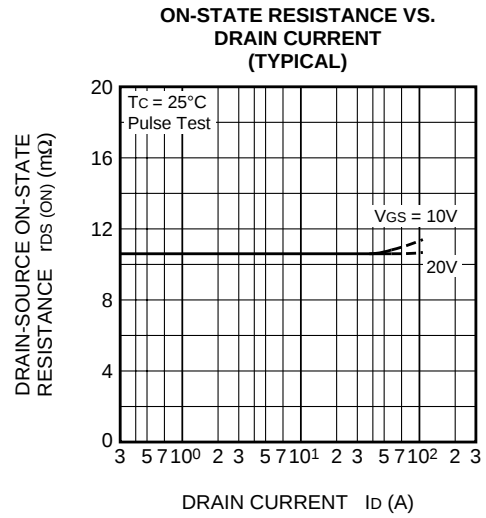
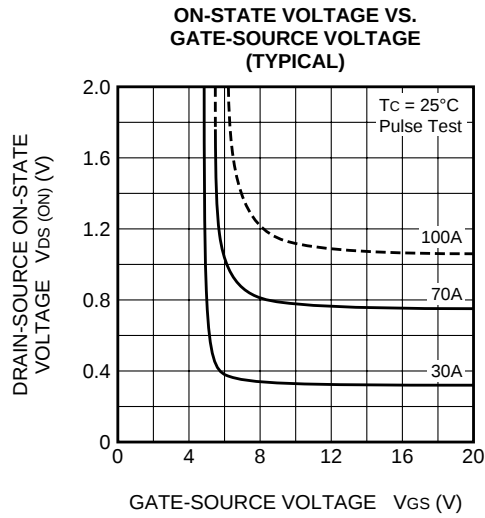


ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

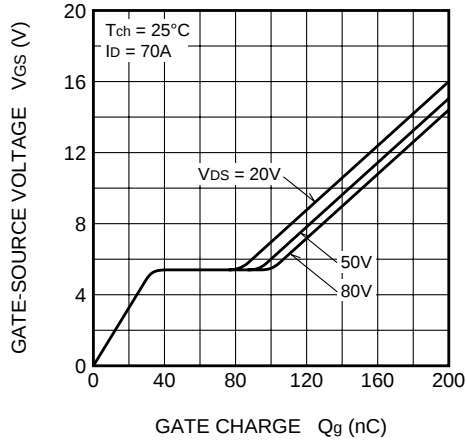
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	100	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±20V, V _{DS} = 0V	—	—	±0.1	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 100V, V _{GS} = 0V	—	—	0.1	mA
V _{GS(th)}	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	2.0	3.0	4.0	V
r _{DS(on)}	Drain-source on-state resistance	I _D = 35A, V _{GS} = 10V	—	14	20	mΩ
V _{DS(on)}	Drain-source on-state voltage	I _D = 35A, V _{GS} = 10V	—	0.49	0.7	V
y _{fs}	Forward transfer admittance	I _D = 35A, V _{DS} = 10V	—	53	—	S
C _{iss}	Input capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	—	6540	—	pF
C _{oss}	Output capacitance		—	1150	—	pF
C _{rss}	Reverse transfer capacitance		—	500	—	pF
t _{d(on)}	Turn-on delay time	V _{DD} = 50V, I _D = 35A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	95	—	ns
t _r	Rise time		—	175	—	ns
t _{d(off)}	Turn-off delay time		—	330	—	ns
t _f	Fall time		—	190	—	ns
V _{SD}	Source-drain voltage	I _S = 35A, V _{GS} = 0V	—	1.0	1.5	V
R _{th(ch-c)}	Thermal resistance	Channel to case	—	—	1.00	°C/W
t _{rr}	Reverse recovery time	I _S = 70A, di _s /dt = -100A/μs	—	120	—	ns

PERFORMANCE CURVES

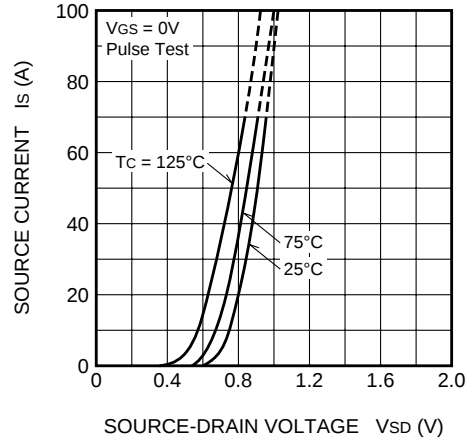




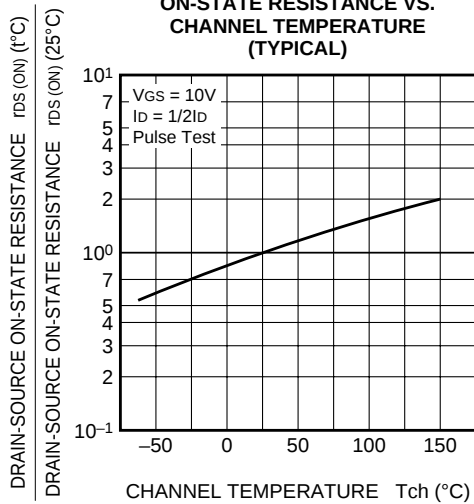
GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)



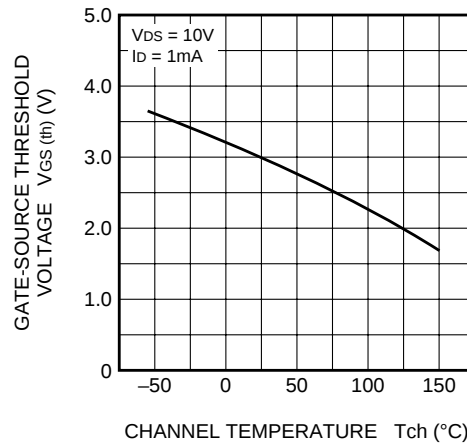
SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



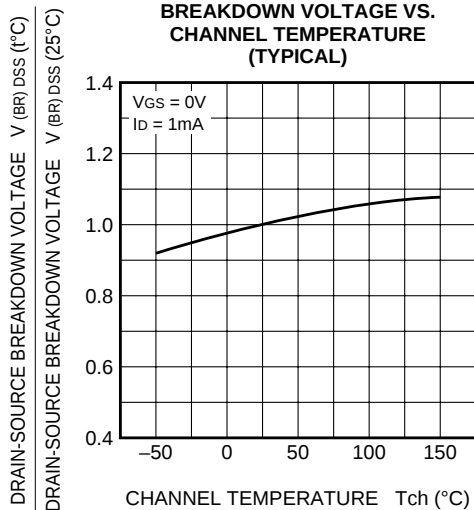
ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)



THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)



TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS

